TRANSISTOR | MOS-FET | IGBT | DIODE

△VBE/△VDS/△VGE/△VCE/△VF 過渡熱抵抗測定器

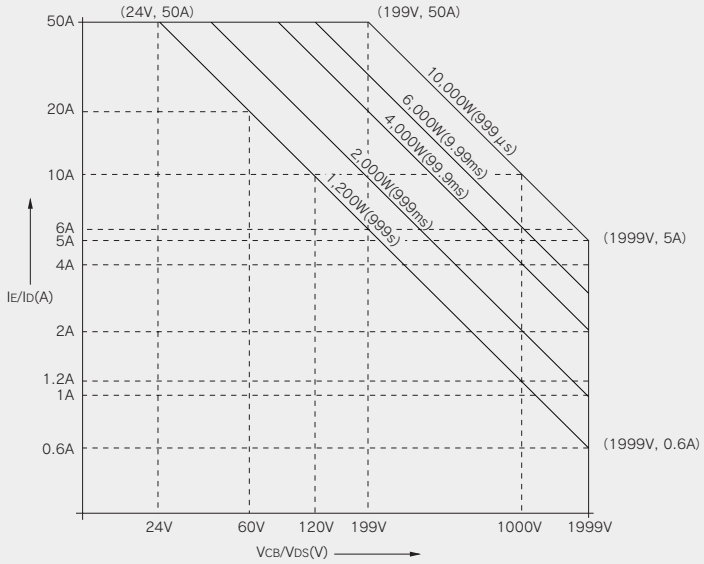
DVFN2050 2000V 50A

●DVFN2050 is thermal resistance test system with forcing voltage 2000V in maximum. It can force 999sec at 1200W line so it is adequate thermal evaluation for power device in high voltage.

●DVFN2050は最大印加電圧2000Vの性能を持つ熱抵抗測定器です。1200Wラインで999secの印加が可能でパワーデバイスの高電圧の熱的評価に最適です。

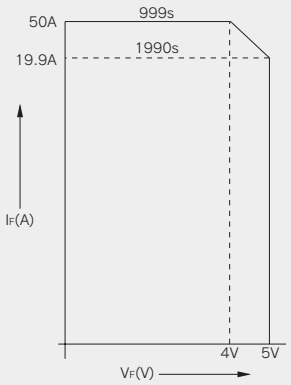
Forcing Power Range Diagram

[TRANSISTOR, IGBT, MOS-FET]

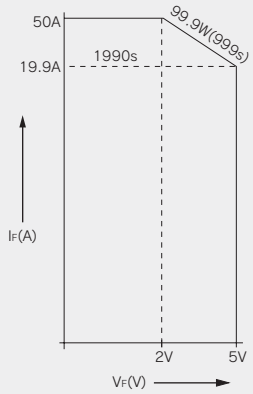


[DIODE]

IF CONSTANT



Power Constant Mode



MODEL	DVFN2050	
MEASUREMENT RANGE		
PRE-TEST	VBE1/VDS1/VF1/VGE1/VCE1	0000mV～9999mV
	ΔVBE/ΔVDS/ΔVF/ΔVGE1/ΔVCE1	0000mV～1999mV
SETTING RANGE		
MEASURABLE DEVICES	NPN/PNP, N/P-MOS FET, N/P-DIODE, N/P-IGBT(GE), N/P-IGBT(CE)	
VCB/VDS	1V～1999V	
IE/ID	1mA～50.0mA	
DIODE FORCING POWER CONSTANT	1.00W～9.99W	
	10.0W～99.9W	
IM	0.1mA～99.9mA	
POWER FORCING TIME(PT)	100μs～999s	
DELAY TIME(DT)	10μs～999μs	
GATE LIMIT(GL)	1.0V～19.9V	
LOWER GATE(LG)/UPPER GATE(UG)	0000mV～1999mV	
BINNING		
OPEN/SHORT CHECK	VF1＞4V…OPEN VF1＜0.2V…SHORT	
BIN INDICATION	PASS, LOW, HIGH, AVAL, REJECT	
DIMENSIONS & WEIGHT	550(W)×860+420(D)×1700(H)…400kg	